

### MPSA55 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 0.625 W ( $T_{amb}=25^{\circ}C$ )

Collector current

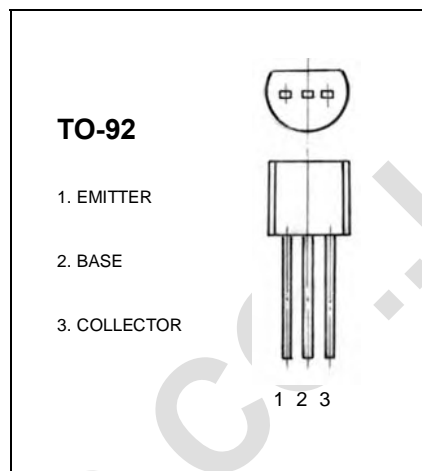
$I_{CM}$ : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$ : -60 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-BASE breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1mA, I_B=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1 mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.1mA, I_C=0$	-4			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60 V, I_E=0$			-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-60V, I_C=0$			-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=-1V, I_C=-100mA$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100 mA, I_B=-10mA$			-0.25	V
Base-Emitter Saturation Voltage	$V_{BE}$	$V_{CE}=-1V, I_C=-100mA$			-1.2	V
Transition frequency	$f_T$	$V_{CE}=-1V, I_C=-100mA$ $f=100MHz$	50			MHz